

Schottky Barrier Rectifier

MBRF20L60CT

FEATURES

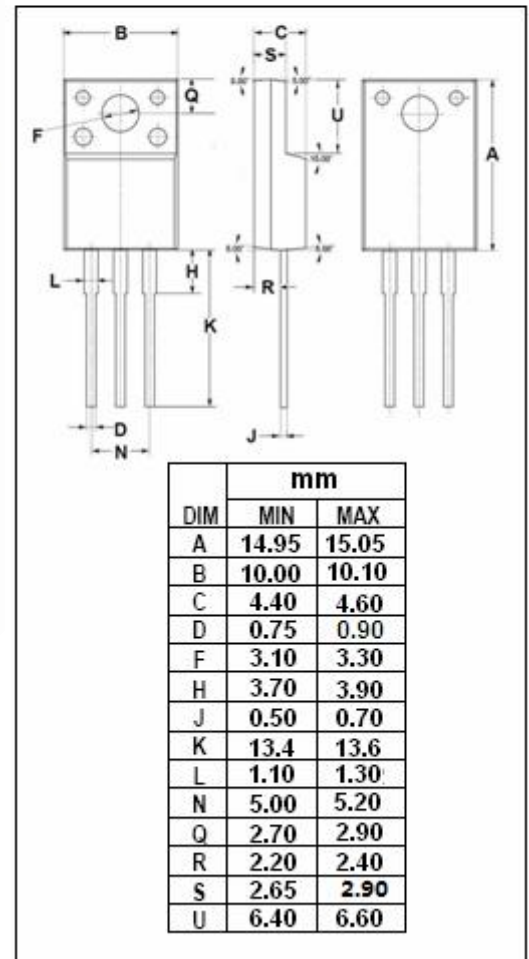
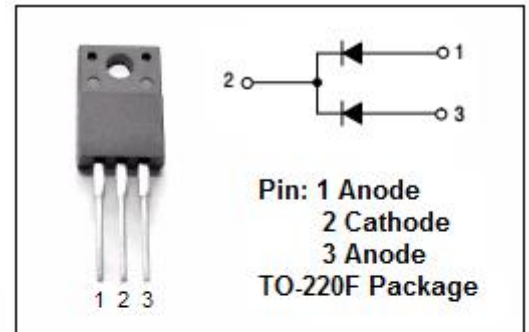
- Schottky barrier chip
- Low Power Loss,High Efficiency
- Guard ring for transient protection
- High Operating Junction Temperature
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- For use in low voltage ,high frequency inverters,free wheeling and polarity protection applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{RRM} V _{RMS} V _R	Peak Repetitive Reverse Voltage RMS Voltage DC Blocking Voltage	60	V
I _{F(AV)}	Average Rectified Forward Current	20	A
I _{FSM}	Nonrepetitive Peak Surge Current 8.3ms single half sine-wave superimposed on rated load conditions	240	A
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-65~175	°C



Schottky Barrier Rectifier**MBRF20L60CT****THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	5.2	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	$I_F = 10\text{A}; T_J = 25^{\circ}\text{C}$	0.57	V
		$I_F = 10\text{A}; T_J = 125^{\circ}\text{C}$	0.54	
		$I_F = 20\text{A}; T_J = 25^{\circ}\text{C}$	0.73	
		$I_F = 20\text{A}; T_J = 125^{\circ}\text{C}$	0.69	
I_R	Maximum Instantaneous Reverse Current	$V_R = V_{RWM}; T_J = 25^{\circ}\text{C}$	380	μA
		$V_R = V_{RWM}; T_J = 125^{\circ}\text{C}$	96	mA